Arrays of widely spaced atomic steps on Si(111) mesas due to sublimation

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Abstract

Steps with spacings of microns form on top of mesas fabricated on Si(111) that is annealed at temperatures where sublimation becomes important. Upon annealing, mesas first develop ridges along their edges, effectively creating craters which then become step-free by a step flow process described in the literature[1,2]. Due to the miscut of the average surface from (111), ridge breakdown occurs on one edge of each mesa as sublimation proceeds. The breakdown point then acts as a source of steps which spread out over the mesa surface. The distribution of steps in the resulting step train depends on the sublimation rate, direct step-step interaction and the diffusive exchange of atoms among the steps. Insight into the role of these processes on the self-organization of the wide terrace distributions is provided by computer simulations using BCF (Burton, Cabrera and Frank) theory. This shows that step spacing can be controlled by varying the annealing temperature and the deposition flux. Comparison of the experimental and predicted step distributions suggest that the dynamics of the widely spaced steps are dominated by sublimation.

Key words: Computer simulations, Atomic force microscopy, Step formation and bunching, Silicon, Single crystal surfaces

1 Introduction

Atomic steps on crystal surfaces are the basic units of surface morphology; by controlling the local density of steps, we can control the surface shape. The contour and density of surface steps can be manipulated by a combination of patterning, which defines the initial step morphology, and thermal annealing, which results in the movement and creation/destruction of steps. The ability

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to guide step dynamics through these processes represents the ultimate limit in height morphology control.

There are many useful applications for surfaces with controlled step morphologies. Due to the changes in coordination at atomic steps, adsorption will usually occur preferentially at those locations. Steps are known to have extremely important effects in nucleation and continued growth of homo- and hetero-epitaxial layers.

Previous work in this field has focused on the creation of large step-free areas. Step-free areas 10-100μm in radius have been formed on Si[3,2,1], SiC[4] and sapphire[5] surfaces by several groups, including our own; these may be useful for making devices that require high quality interfaces[6] as well as providing model surfaces to investigate nucleation and defect properties[7]. But arrays of steps that have controlled spacing in the micron range may also have use in applications such as templates for nanowires or organic thin films. Their study may also lead to better models of step dynamics for weakly interacting steps.

Widely spaced steps are difficult to make because orientational errors of 0.1° or more are usually introduced in aligning crystals during polishing, resulting in vicinal surfaces with terrace widths in the 100nm range on Si(111). To successfully create such arrays, an understanding of step dynamics is required to effectively redistribute the steps. For Si(111), previous literature has focused on understanding the role of electromigration[8] and the Ehrlich-Schwoebel[9,10] effect in creating step bunches.

In this Paper, we describe an experiment in which mesa structures (areas that are completely surrounded by trenches) on Si(111) were annealed at temperatures over 925°C in ultrahigh vacuum to produce arrays of steps with spacing of 1μm or more. In our discussion, we show that these arrays arise through transient ridge formation around the edges of the mesas followed by redistribution of the steps on top of the mesa after ridge breakdown.

2 Experimental

Si(111) was patterned by standard optical lithographic methods using silicon oxide as an etch mask. Mesa structures with different azimuthal orientations and size were etched into silicon by reactive ion etching. The etch depth was around 2μm for all of our samples. 15mm$\times$5mm samples were cut from the wafer using a diamond tip scriber. The samples were dipped in HF for 3 minutes to remove any residual oxide and to hydrogen terminate the surface before being loaded into the vacuum chamber.

The samples were heated by direct current in a UHV system (base pressure 10^{-10} Torr) while the temperature was monitored with a pyrometer. Some samples were subjected to flashing above 1200°C to quickly remove the native oxide layer before annealing while others were annealed without flashing. The annealing temperature ranged from 925°C to 1150°C. After annealing, the samples were taken out of the vacuum chamber and imaged by AFM in air.

3 Results & Discussion

Fig. 1(a) shows an example of the typical height profile of mesas after annealing. Ridges have formed along most of the edges of the mesas. The portion of the edge without a ridge act as a step source for the widely separated step arrays that develop on the mesa tops. The step arrays formed through this process showed similar step spacing on other mesas on the sample that were of the same size and orientation.

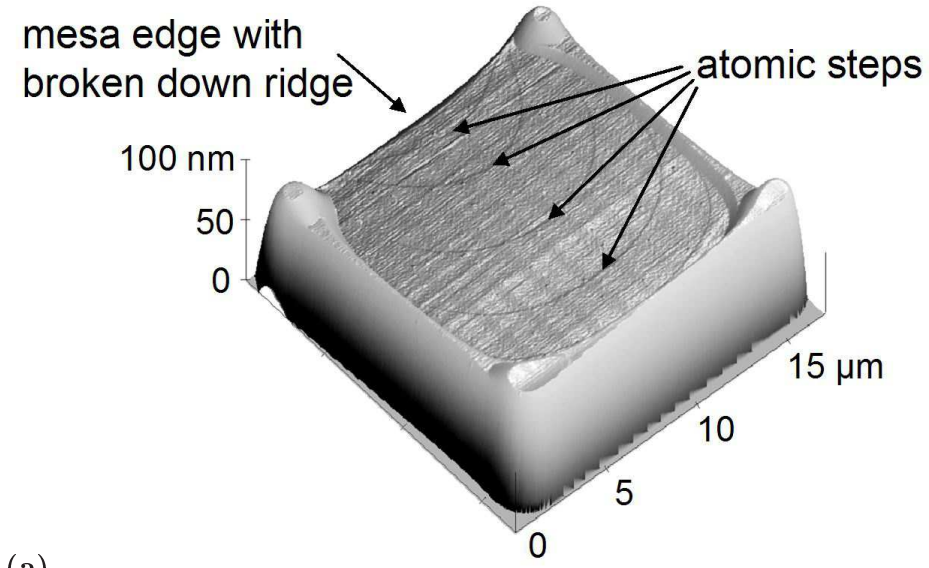
From a series of rotated mesas patterned on the sample, we also find that the length of the mesa edge without a ridge increases dramatically as the mesa edge becomes nearly parallel to the miscut axis as illustrated in Fig. 1(b). The crystallographic directions of the mesa edges do not affect the amount of ridge breakdown. The direction of the DC heating current (and hence electromigration effects) also appears to be unimportant, and in fact similar results were obtained with low frequency (0.2 Hz) AC heating.

We will look at the two stages in the formation of the step arrays viz (i) the development and breakdown of ridges along the mesa edges and (ii) the generation of widely spaced steps across the mesas.

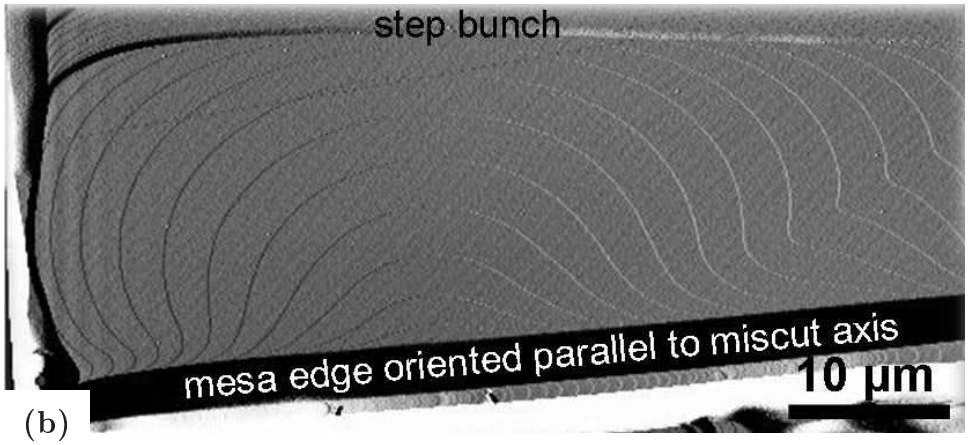
3.1 Spontaneous Ridge Formation on Mesa Edges

The formation of ridges along the edges of mesas is predicted[11] by the classical Mullins theory[12,13] based on the tendency of the material to eliminate chemical potential gradients associated with high curvature at the mesa edges. However, Mullins theory is expected to be applicable above the roughening temperature whereas our experiments were performed below the roughening temperature of the Si(111) surface. When below the roughening temperature, the elimination of the sharp edges requires mass flow to the mesa top that results in either the formation of new islands or incorporation of atoms into pre-existing steps. [1]

[1] For this to occur, the roughening temperature only needs to be exceeded for a range of surface orientations between the mesa top and the sidewall.



(a)



(b)

Fig. 1. (a) Height profile of a mesa on Si(111) that has been annealed at 1000°C for 1 hour followed by flashing at 1220°C for 20 seconds. Note that a ridge exists along three edges of the mesa. (b) Deflection AFM image of step arrays formed on top of a rectangular mesa on Si(111) after flashing at 1250°C followed by annealing at 1100°C for 15 minutes.

Mullins, Rohrer[14,15] and Combe[16] have considered the case where ridge formation requires that new islands have to be nucleated on the mesa surface; they conclude that once the radius of curvature of the edge exceeds ∼1nm, the free energy barrier for further island nucleation process becomes prohibitively large.

However, the existence of miscut steps on the mesa top can significantly reduce the barrier for ridge formation if the transfer of atoms occurs to these existing steps; we believe this to be the most likely mechanism on these patterned surfaces. Thus ridges can be produced by modification of the shape of the

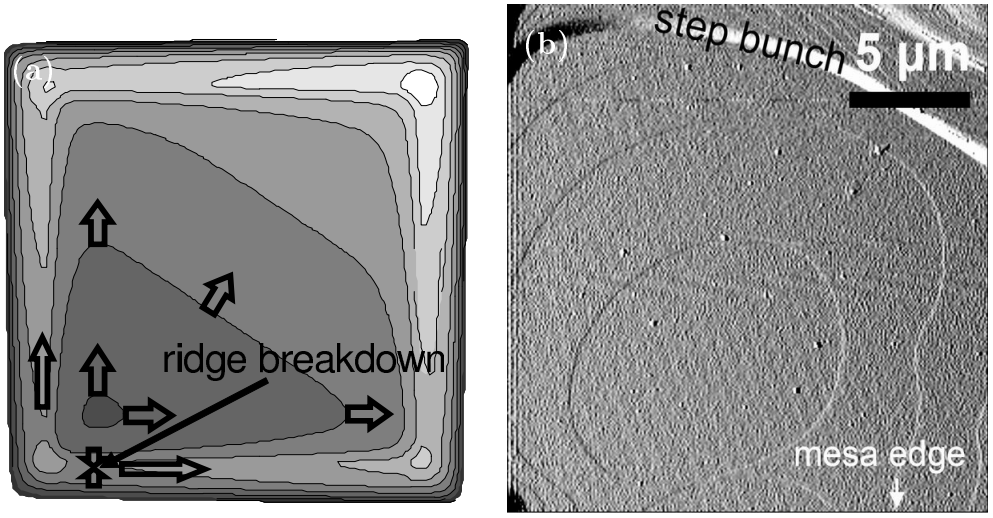


Fig. 2. (a) Step motion on top of the mesa after mesa edges have rounded enough to slow diffusion-induced ridge formation. Ridges convert the centers of the mesa into craters and the steps forming these craters expand outwards to create a central step-free area. (b) Steps near an edge of a mesa on Si(111) after flashing at 1400°C and quenching. The circular steps are similar to those previously reported[3,2] for craters surrounded by patterned ridges.

miscut steps on the mesa top.

The formation of ridges by this process is qualitatively different from that predicted by the classical Mullins theory because the ridge height will be dependent on the number of miscut steps near the mesa edge. This is in line with our observation of ridges on the mesa that is aligned with the miscut steps. Near the lower edge, a ridge of lower height forms and can subsequently disappear as sublimation proceeds.

The mass flow from the edges and the corners of the mesa that creates ridges will slow down as the radius of curvature of the edges increase. Such a structure is illustrated in Fig. 2(a). During sublimation, the steps forming the ridges will retract toward a corner of the mesa, resulting in configurations of steps of both signs. The steps on top of the ridge will eventually meet the opposite sign step on the other side of the ridge, resulting in a reduction of its height. Repetition of this process will result in ridge breakdown.

While the ridge is evolving, the slight depression on the mesa, formed by ridge enclosure, begins to become step-free due to sublimation. When the ridge finally breaks down, a low step density region, bounded by step bunches, is formed. A possible snapshot of this process on a sample that had been flashed to 1400°C and quickly quenched is shown in Fig. 2(b).

After ridge breakdown, widely spaced step arrays form on the mesas and persist even after long annealing times in which hundreds of atomic layers of the crystal are removed [2]. To better understand the development of these arrays, computer simulation based on the Burton-Cabrera-Frank theory[17] were used to model the evolution of widely spaced steps bounded by step bunches as illustrated in Fig. 3(a). Our system was assumed to be composed only of steps with the same sign, so that step annihilation does not occur; the 2-dimensional step arrays were approximated as 1-dimensional, which should be a reasonable approximation for the steps moving in from the middle of the gap since the radius of curvature of those steps is so large. In the BCF theory with the quasi-static approximation, the adatom concentration c, on the terraces satisfies the equation

$$D\frac{\partial^2 c}{\partial x^2} - \frac{c}{\tau} + F = 0 \tag{1}$$

where D is the diffusion constant of the adatoms, $1/\tau$ is the rate of evaporation and F is the flux of atoms condensing on the surface per unit time. (For the experiment reported here $F = 0$.) The boundary conditions for step n at x_n is given by

$$D\left.\frac{\partial c_n}{\partial x}\right|_{x_n} = +K_+\left(c_n(x_n) - c_n^{eq}\right) \tag{2}$$

$$D\left.\frac{\partial c_{n-1}}{\partial x}\right|_{x_n} = -K_-\left(c_{n-1}(x_n) - c_n^{eq}\right) \tag{3}$$

where $c_n(x)$ is the adatom concentration between steps $n+1$ and n, $K_\pm$ are the adatom attachment-detachment rate constants from the upper and lower terraces. Values of K_+ and K_- that are different from each other model the Ehrlich-Schwoebel barrier. c_n^{eq} is the equilibrium concentration of adatoms at step n; $c_n^{eq} \approx c_0^{eq}(1 + \beta\Delta\mu_n)$ where c_0^{eq} is the equilibrium concentration of adatoms at a single isolated straight step, $\beta = 1/k_BT$, and $\Delta\mu_n$ is the free energy change involved in adding an adatom to step n (incorporating the step-step interactions) from an isolated step.

Solving the set of differential equations for the adatom concentration with the boundary conditions give the adatom concentration on the terraces. The

[2] The highest annealing temperature of 1100°C results in the removal of a bilayer every 5 seconds. We have done anneals for 2 hours at this temperature and still get widely spaced step arrays.

gradients of the adatom concentration give the fluxes of adatoms into the steps from the terraces to the left and right of the step, determining the step velocity. The result can be written by first defining the following two functions,

$$\Phi_n^{\pm} = \frac{\tanh(\widetilde{l}_n/2) + d_{\pm}}{(d_+ + d_-)\coth(\widetilde{l}_n) + (1 + d_- d_+)} \tag{4}$$

$$\Gamma_n = \frac{\Delta\mu_{n+1} - \Delta\mu_n}{(d_+ + d_-)\cosh(\widetilde{l}_n) + (1 + d_- d_+)\sinh(\widetilde{l}_n)} \tag{5}$$

where the lengths are rescaled by the diffusion length $x_s = \sqrt{D\tau}$ so that $\widetilde{l}_n = (\widetilde{x}_{n+1} - \widetilde{x}_n)/x_s$ is the terrace width between steps $n+1$ and n and $d_{\pm} = (D/K_{\pm})/x_s$ is the rescaled attachment-detachment length which represents how far the adatom must diffuse at the step edges before attaching to the step. The step chemical potential is defined as $\Delta\mu_n = 2g\Omega(\widetilde{l}_{n-1}^{-3} - \widetilde{l}_n^{-3})/x_s^3$ where g is the step interaction energy per unit length of step. The step velocity is then

$$\frac{d\widetilde{x}_n}{d\widetilde{t}} = (1 - f + \beta\Delta\mu_n)\left[\Phi_n^- + \Phi_{n-1}^+\right] + \beta\left[\Gamma_{n-1} - \Gamma_n\right] \tag{6}$$

where $\widetilde{t} = c_{eq}^0 \Omega t/\tau$ is in units of the time required to evaporate a monolayer from a crystal in vacuum while $f = F\tau/c_{eq}^0$ is the rescaled deposition flux.

To easily relate our simulation results to experiment, we will consider the dynamics in terms of the terrace widths. The rate of change of a terrace width, $\widetilde{l}_n$, can be written as $d\widetilde{l}_n/d\widetilde{t} = d\widetilde{x}_{n+1}/d\widetilde{t} - d\widetilde{x}_n/d\widetilde{t}$. This equation was used to simulate the behavior of an array of terrace widths. Four parameters, g, $d_{\pm}$ and f are needed to numerically integrate this system of differential equations. We set $f = 0$ to model a sublimating surface without any deposition and take $g = 5\text{meV\AA}$[18], $x_s = 20\mu$m[19] from the literature.

We consider the evolution, as sublimation proceeds, of a set of terraces that exist between the mesa edge and a step bunch on the mesa. We take various values of $d_{\pm}$ to investigate the effect of attachment-detachment rates on the terrace width distribution. Steps move in from the mesa edge and incorporate into the step bunch on the mesa so periodic boundary conditions are assumed. The changes in terrace width distribution over time are displayed in Fig. 3(b) as a series of plots of terrace index (or terrace height in units of step height) versus the terrace width. The simulation results in a 'pulse' of terrace widths which move down along the index axis as annealing progresses.

In the simulation, the pulses seem to self-organize to a stable distribution over time. With the inclusion of the Ehrlich-Schwoebel effect ($d_+ > d_-$) for small $d_{\pm}$, the pulse is distributed over a large number of terraces and decays slowly in amplitude, while for large $d_{\pm}$, the pulse is formed by a few terraces and

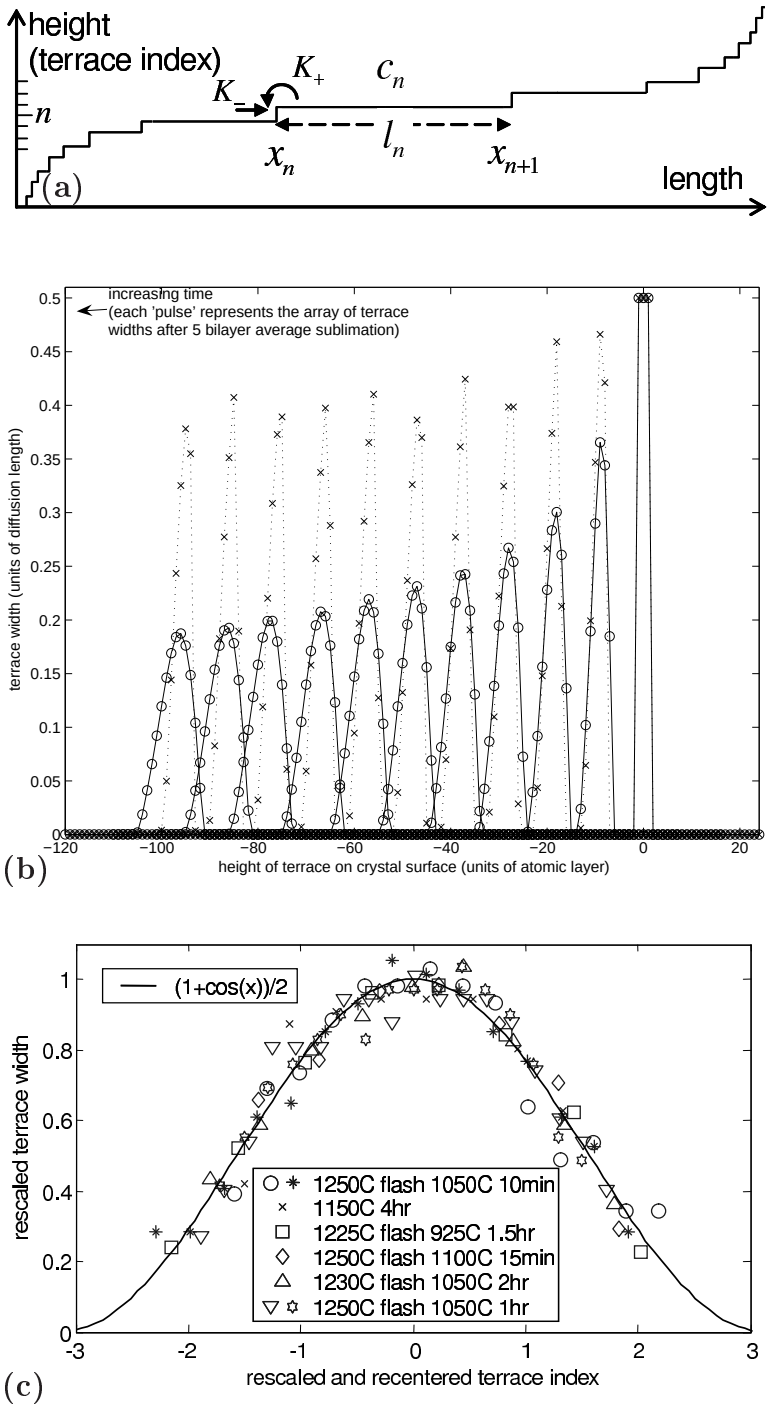


Fig. 3. (a) Diagram of the model for computer simulations. The terrace distribution of a region of low step density bounded by step bunches as shown is investigated. (b) Computer simulation results for the evolution of the terrace distribution for the initial configuration of 3 terraces $0.5x_s$ wide bounded by step bunches with $10^{-4}x_s$ step spacing when $d_+ = 10^{-6}$, $d_- = 0$ (solid line) and $d_+ = 0.1$, $d_- = 0.05$ (dotted line) plotted in increments of the time to evaporate 5 bilayers. (c) Experimental data showing rescaled terrace index (recentered at the maximum terrace width) versus terrace width fitted to a cosine curve for 8 mesas on 6 samples annealed under different conditions. This suggests that the terrace length scale for the widely spaced steps in our experiments is in the sublimation limited regime.

quickly becomes stable. By considering fluctuations on a train of steps, all with the same initial terrace widths, stable pulse formation was predicted by Misbah[20] and Sato[21] through analysis of the BCF equation. In the present Paper, the physical argument for pulse formation is presented for a train of steps that have a wide range of terrace widths; This allows us to form stable pulses much faster in our computer simulations.

There are two main physical causes for terrace width redistribution. For step trains with small terraces, the step motion is driven by adatom exchange between neighboring steps due to step-step interaction which tries to equalize the terrace widths of the step train. This is the case when the second term in Eq. (6) dominates. The decay rate of fluctuations in terrace widths depends on various limiting adatom kinetics as discussed in detail by Liu[22].

For step trains with large terraces, the step motion is driven by sublimation of adatoms from the terraces. This is the case when the first term in Eq. (6) dominates, and it should be noted that the terrace widths which result in crossover to this behavior can be controlled by adjusting the magnitude of the deposition flux, F. Sublimation dominated step motion has sub-regimes depending on the limiting adatom kinetics.

When the terrace widths are small($\widetilde{l} < \sqrt{2(d_+ + d_-)}$), the number of adatoms evaporating from the terraces may be limited by the attachment-detachment rates at the step. In this attachment-detachment limited(ADL) regime, the terrace widths in the pulse evolve as described by the equation

$$\frac{d\widetilde{l}_n}{d\widetilde{t}} = \frac{(1-f)}{2}\left[\widetilde{l}_{n+1} - \widetilde{l}_{n-1} + \delta(2\widetilde{l}_n - \widetilde{l}_{n+1} - \widetilde{l}_{n-1})\right] \tag{7}$$

where $\delta = (d_+ - d_-)/(d_+ + d_-)$. Due to the last term, this equation yields dispersive traveling wave solutions; fluctuations in terrace width increase in amplitude with time if $d_+ > d_-$. This corresponds to the well-known result[23] that the terrace width distribution is unstable under sublimation with the Ehrlich-Schwoebel effect.

For wider terrace widths($\sqrt{2(d_+ + d_-)} < \widetilde{l} < 1$), the number of adatoms subliming from the terraces is limited by the sublimation rate. In the sublimation limited(SL) regime, the terrace widths in the pulse evolve as described by the equation

$$\frac{d\widetilde{l}_n}{d\widetilde{t}} = \frac{(1-f)}{2}\left[\widetilde{l}_{n+1} - \widetilde{l}_{n-1}\right] \tag{8}$$

which preserves any fluctuation in terrace widths and propagates it down the crystal layers as annealing proceeds [3] .

The main insight provided by these approximations is that the dynamics governing the evolution of a system of steps depends on the range of terrace widths involved. For closely spaced steps, step-step interaction dominates while for very widely spaced steps, SL dynamics dominates. ADL dynamics dominates for step spacings that are between these two regimes.

To understand how these different dynamics regimes work together to produce a stable pulse in terrace width (plotted versus the terrace index), we should note that fluctuations in the terrace widths in the ADL regime will increase in amplitude with time. For a sinusoidal fluctuation, this will result in the maximum terrace widths in the array becoming larger and the minimum terrace widths becoming smaller with time.

Since the ADL regime is bounded by the step-step interaction and the DL regime, this amplitude increase cannot continue. Sooner or later, the terraces will get small enough to enter the step-step interaction regime and prevent further growth of the fluctuation. The interaction between ADL and step-step interaction dynamics that result in stable pulses has also been demonstrated mathematically in other papers[24].

The important new result in our paper is that for systems with low average step density, the ADL dynamics can cause the maximum terrace widths to become large enough to enter the SL regime. The subsystem of steps in this SL regime will be subjected to boundary conditions set by the ADL dynamics, resulting in a pulse with a sinusoidal profile as shown in the solid line plots in Fig. 3(b). If the constraint of the system size is such that the SL regime cannot be reached, a pulse with a sharp peak will be formed as shown by the dotted plots in Fig. 3(b). Thus, a pulse of terrace widths will always self-organize into a configuration that balances the decay of fluctuations in the step-step interaction regime with the amplification of fluctuations in the ADL regime.

We can analyze our experimental results to see if the reduction of step density on the mesa tops due to ridge formation and breakdown enabled the SL regime to be reached for the terrace width distributions observed in our experiments. If this is the case, a sinusoidal profile should be obtained if we plot the terrace index versus terrace width. Rescaled plots of terrace widths observed on 8 different mesas for 6 samples annealed under different conditions are shown in Fig. 3(c). The data suggest that the dynamics correspond to the SL regime over the wide terraces; the evidence is not totally conclusive since the step bunches are not oriented exactly parallel to the mesa edge in most of our

[3] The diffusion limited regime, when $\widetilde{l} \gg 1$, is omitted for simplification. In this regime, $d\widetilde{l}_n/d\widetilde{t} = 0$

measurements, and curved step bunches may behave somewhat differently. We may also have some step redistribution during quenching that tends to even out the terrace distributions.

From our theoretical analysis, we can infer that the annealing temperature and the deposition flux will affect the magnitude of the terrace widths at which crossover occurs between the different dynamics regimes; this will allow a degree of control over the number and the width of the widely spaced terraces in the step array. For example, lower annealing temperature will favor ADL dynamics, resulting in fewer and wider terraces in the step array as is indeed seen in our experimental results.

4 Summary

In summary, we have shown that novel widely spaced arrays of steps can be produced through sublimation on top of fabricated mesa structures. A key feature of the process is the initial formation of a ridge around the top of each mesa in order to eliminate the large chemical potential gradients associated with the edge. The presence of this ridge allows the center of the mesa to become almost step-free. As the ridges widen by diffusion, sublimation eventually takes over and causes the elimination of the ridge and the intrusion of steps from the edge onto the mesa surface. The new array of steps has a terrace width distribution that persists for long annealing times. Computer simulations of the initial low step density area on the mesa suggests that the widely spaced step arrays decay very slowly in the sublimation limited regime and evolve toward a stable terrace width distribution. We also find that a degree of control may be exercised over number of terraces in the low step density region and their widths by varying the annealing temperature and the deposition flux. This provides a new method of fabricating controlled step arrays that can be used as templates. Observing the evolution of these systems of steps may also provide new insights into the important kinetic process governing the dynamics of steps.

Acknowledgements

We acknowledge discussions with Prof. J.P. Sethna and the extensive use of the Cornell Nanofabrication Facility for making samples. This work is supported by NSF grant no. DMR-0109641 and by grant DMR-9632275 through the Cornell Center for Materials Research.

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